

9A High-Speed MOSFET Drivers

Features

- · High Peak Output Current: 9A
- · Wide Input Supply Voltage Operating Range:
 - 4.5V to 18V
- · High Continuous Output Current: 2A Max
- · Fast Rise and Fall Times:
 - 30 ns with 4,700 pF Load
 - 180 ns with 47,000 pF Load
- · Short Propagation Delays: 30 ns (typ)
- Low Supply Current:
 - With Logic '1' Input 200 μA (typ)
 - With Logic '0' Input 55 μA (typ)
- Low Output Impedance: 1.4Ω (typ)
- Latch-Up Protected: Will Withstand 1.5A Output Reverse Current
- Input: Will Withstand Negative Inputs Up To 5V
- Pin-Compatible with the TC4420M/TC4429M 6A MOSFET Driver
- Wide Operating Temperature Range:
 - -55°C to +125°C
- See TC4421/TC4422 Data Sheet (DS21420) for additional temperature range and package offerings

Applications

- · Line Drivers for Extra Heavily-Loaded Lines
- Pulse Generators
- · Driving the Largest MOSFETs and IGBTs
- · Local Power ON/OFF Switch
- · Motor and Solenoid Driver

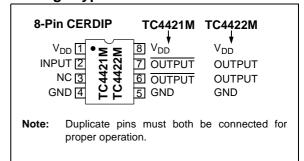
General Description

The TC4421M/TC4422M are high-current buffer/ drivers capable of driving large MOSFETs and IGBTs.

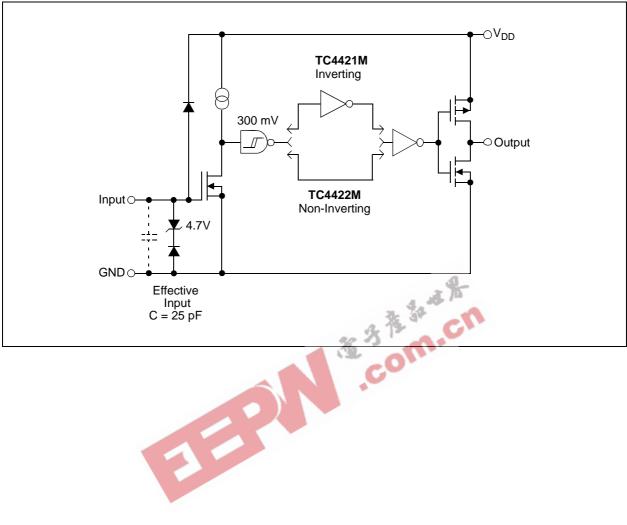
They are essentially immune to any form of upset, except direct overvoltage or over-dissipation. They cannot be latched, under any conditions, within their power and voltage ratings. These parts are not subject to damage or improper operation when up to 5V of ground bounce is present on their ground terminals. They can accept, without damage or logic upset, more than 1A inductive current of either polarity being forced back into their outputs. In addition, all terminals are fully protected against up to 4 kV of electrostatic discharge.

The TC4421M/TC4422M inputs may be driven directly from either TTL or CMOS (3V to 18V). In addition, 300 mV of hysteresis is built into the input, providing noise immunity and allowing the device to be driven from slowly rising or falling waveforms.

Package Types



Functional Block Diagram



1.0 ELECTRICAL CHARACTERISTICS

Absolute Maximum Ratings†

Supply Voltage	+20V
Input Voltage	$(V_{DD} + 0.3V)$ to $(GND - 5V)$
Input Current (V _{IN} > V _{DD}).	50 mA

† Stresses above those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions above those indicated in the operation sections of the specifications is not implied. Exposure to Absolute Maximum Rating conditions for extended periods may affect device reliability.

DC CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.									
Parameters	Sym	Min	Тур	Max	Units	Conditions			
Input									
Logic '1', High Input Voltage	V _{IH}	2.4	1.8		V				
Logic '0', Low Input Voltage	V_{IL}	_	1.3	0.8	V				
Input Current	I _{IN}	-10	_	+10	μΑ	$0V \le V_{IN} \le V_{DD}$			
Output									
High Output Voltage	V_{OH}	V _{DD} – 0.025	_	-250	V	DC TEST			
Low Output Voltage	V_{OL}	_	_	0.025	V	DC TEST			
Output Resistance, High	R _{OH}	_	1.4	~ <u>)</u>	Ω	$I_{OUT} = 10 \text{ mA}, V_{DD} = 18V$			
Output Resistance, Low	R_{OL}		0.9	1.7	Ω	$I_{OUT} = 10 \text{ mA}, V_{DD} = 18V$			
Peak Output Current	I_{PK}		9.0		Α	V _{DD} = 18V			
Latch-Up Protection Withstand Reverse Current	REV	•	>1.5	_	А	Duty cycle \leq 2%, t \leq 300 µsec			
Switching Time (Note 1)									
Rise Time	t _R	_	60	75	ns	Figure 4-1 , C _L = 10,000 pF			
Fall Time	t _F	_	60	75	ns	Figure 4-1 , C _L = 10,000 pF			
Delay Time	t _{D1}	_	30	60	ns	Figure 4-1			
Delay Time	t _{D2}	_	33	60	ns	Figure 4-1			
Power Supply									
Power Supply Current	I _S	_	0.2	1.5	mA	V _{IN} = 3V			
		_	55	150	μΑ	$V_{IN} = 0V$			
Operating Input Voltage	V_{DD}	4.5	_	18	V				

Note 1: Switching times ensured by design.

DC CHARACTERISTICS (OVER OPERATING TEMPERATURE RANGE)

Electrical Specifications: Unless otherwise noted, over operating temperature range with $4.5V \le V_{DD} \le 18V$.								
Parameters	Sym	Min	Тур	Max	Units	Conditions		
Input								
Logic '1', High Input Voltage	V _{IH}	2.4	_	_	V			
Logic '0', Low Input Voltage	V_{IL}	_	_	0.8	V			
Input Current	I _{IN}	-10	_	+10	μΑ	$0V \le V_{IN} \le V_{DD}$		
Output								
High Output Voltage	V _{OH}	V _{DD} – 0.025	_	_	V	DC TEST		
Low Output Voltage	V _{OL}	_	_	0.025	V	DC TEST		
Output Resistance, High	R _{OH}	_	2.4	3.6	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Output Resistance, Low	R _{OL}	_	1.8	2.7	Ω	I _{OUT} = 10 mA, V _{DD} = 18V		
Switching Time (Note 1)								
Rise Time	t _R	_	60	120	ns	Figure 4-1 , C _L = 10,000 pF		
Fall Time	t _F	_	60	120	ns	Figure 4-1 , C _L = 10,000 pF		
Delay Time	t _{D1}	_	50	80	ns	Figure 4-1		
Delay Time	t _{D2}	_	65	80	ns 🦣	Figure 4-1		
Power Supply								
Power Supply Current	I _S	_	_	3	mA	V _{IN} = 3V		
			. 1	0.2	.01	V _{IN} = 0V		
Operating Input Voltage	V_{DD}	4.5	-+	18	V			

Note 1: Switching times ensured by design.

TEMPERATURE CHARACTERISTICS

Electrical Specifications: Unless otherwise noted, all parameters apply with $4.5V \le V_{DD} \le 18V$.							
Parameters	Sym	Min	Тур	Max	Units	Conditions	
Temperature Ranges							
Specified Temperature Range (M)	T _A	-55	_	+125	°C		
Maximum Junction Temperature	TJ	_	_	+150	°C		
Storage Temperature Range	T _A	-65	_	+150	°C		
Package Thermal Resistances							
Thermal Resistance, 8L-CERDIP	θ_{JA}	_	150	_	°C/W		

2.0 TYPICAL PERFORMANCE CURVES

Note: The graphs and tables provided following this note are a statistical summary based on a limited number of samples and are provided for informational purposes only. The performance characteristics listed herein are not tested or guaranteed. In some graphs or tables, the data presented may be outside the specified operating range (e.g., outside specified power supply range) and therefore outside the warranted range.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with $4.5V \le V_{DD} \le 18V$.

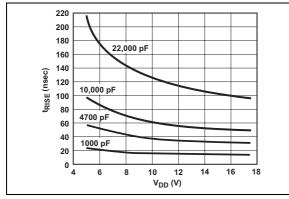


FIGURE 2-1: Rise Time vs. Supply Voltage.

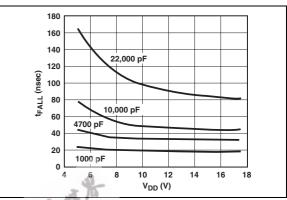


Figure 2-4: Fall Time vs. Supply Voltage.

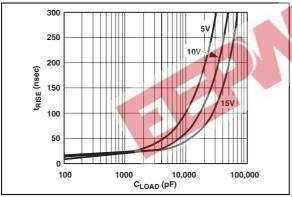


FIGURE 2-2: Rise Time vs. Capacitive Load.

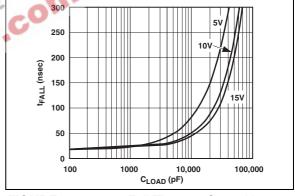


FIGURE 2-5: Fall Time vs. Capacitive Load.

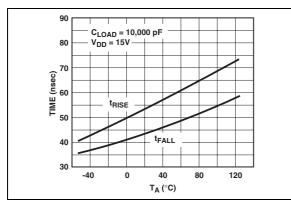


FIGURE 2-3: Rise and Fall Times vs. Temperature.

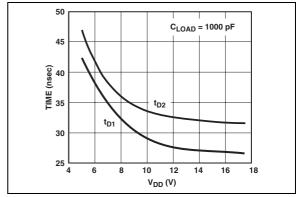


FIGURE 2-6: Propagation Delay vs. Supply Voltage.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with 4.5V $\leq V_{DD} \leq 18V$.

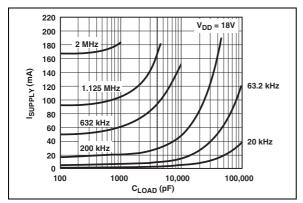


FIGURE 2-7: Supply Current vs. Capacitive Load ($V_{DD} = 18V$).

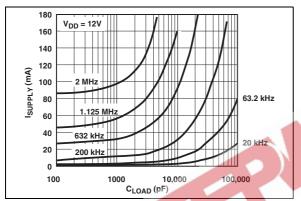


FIGURE 2-8: Supply Current vs. Capacitive Load ($V_{DD} = 12V$).

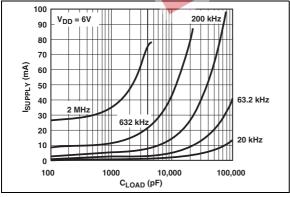


FIGURE 2-9: Supply Current vs. Capactive Load $(V_{DD} = 6V)$.

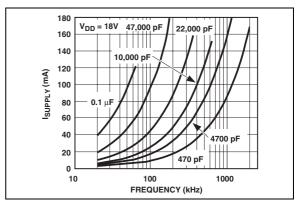


FIGURE 2-10: Supply Current vs. Frequency $(V_{DD} = 18V)$.

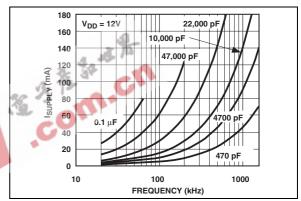


FIGURE 2-11: Supply Current vs. Frequency $(V_{DD} = 12V)$.

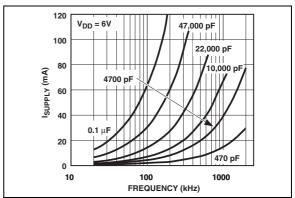


FIGURE 2-12: Supply Current vs. Frequency $(V_{DD} = 6V)$.

Note: Unless otherwise indicated, $T_A = +25^{\circ}C$ with 4.5V $\leq V_{DD} \leq 18V$.

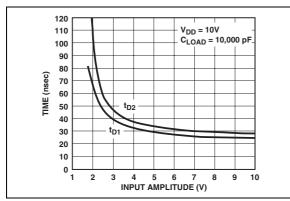


FIGURE 2-13: Propagation Delay vs. Input Amplitude.

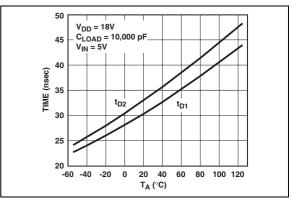


FIGURE 2-16: Propagation Delay vs. Temperature.

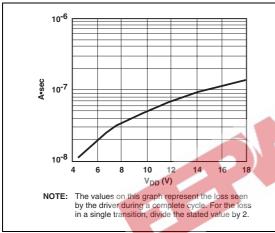


FIGURE 2-14: Crossover Energy vs. Supply Voltage.

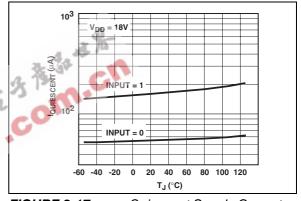


FIGURE 2-17: Quiescent Supply Current vs. Temperature.

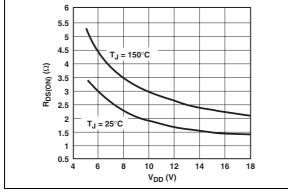


FIGURE 2-15: High-State Output Resistance vs. Supply Voltage.

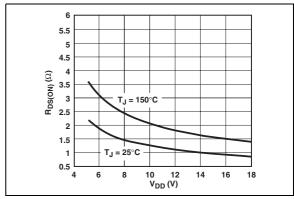


FIGURE 2-18: Low-State Output Resistance vs. Supply Voltage.

3.0 PIN DESCRIPTIONS

The descriptions of the pins are listed in Table 3-1.

TABLE 3-1: PIN FUNCTION TABLE

Pin No. 8-Pin CERDIP	Symbol	Description
1	V_{DD}	Supply input, 4.5V to 18V
2	INPUT	Control input, TTL/CMOS-compatible input
3	NC	No connection
4	GND	Ground
5	GND	Ground
6	OUTPUT	CMOS push-pull output
7	OUTPUT	CMOS push-pull output
8	V_{DD}	Supply input, 4.5V to 18V

3.1 Supply Input (V_{DD})

The V_{DD} input is the bias supply for the MOSFET driver and is rated for 4.5V to 18V with respect to the ground pin. The V_{DD} input should be bypassed to ground with a local ceramic capacitor. The value of the capacitor should be chosen based on the capacitive load that is being driven. A minimum value of 1.0 μ F is suggested.

3.2 Control Input

The MOSFET driver input is a high-impedance, TTL/CMOS-compatible input. The input also has 300 mV of hysteresis between the high and low thresholds that prevents output glitching even when the rise and fall time of the input signal is very slow.

3.3 CMOS Push-Pull Output

The MOSFET driver output is a low-impedance, CMOS, push-pull style output capable of driving a capacitive load with 9.0A peak currents. The MOSFET driver output is capable of withstanding 1.5A peak reverse currents of either polarity.

3.4 Ground

The ground pins are the return path for the bias current and for the high peak currents that discharge the load capacitor. The ground pins should be tied into a ground plane or have very short traces to the bias supply source return.

4.0 APPLICATIONS INFORMATION

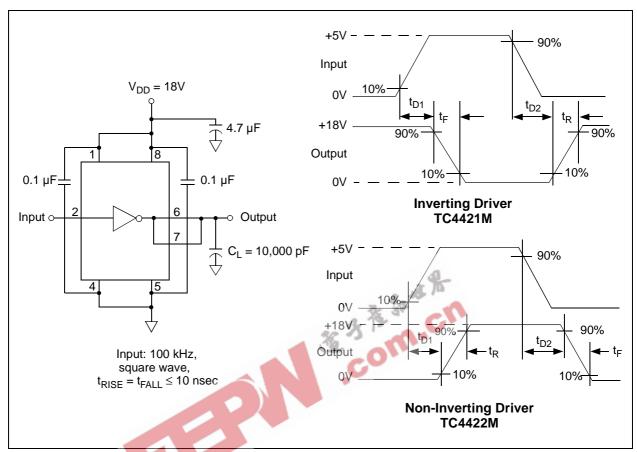
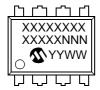


FIGURE 4-1: Switching Time Test Circuits.

5.0 PACKAGING INFORMATION

5.1 Package Marking Information

8-Lead CERDIP (300 mil)









Legend: XX...X Customer-specific information

Y Year code (last digit of calendar year)
YY Year code (last 2 digits of calendar year)
WW Week code (week of January 1 is week '01')

NNN Alphanumeric traceability code

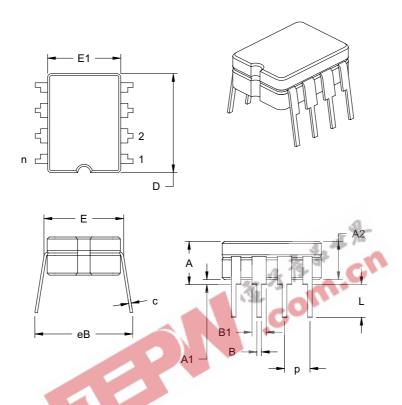
(e3) Pb-free JEDEC designator for Matte Tin (Sn)

This package is Pb-free. The Pb-free JEDEC designator (e3)

can be found on the outer packaging for this package.

Note: In the event the full Microchip part number cannot be marked on one line, it will be carried over to the next line, thus limiting the number of available characters for customer-specific information.

8-Lead Ceramic Dual In-line - 300 mil (CERDIP)



	Units		INCHES*		MILLIMETERS		
Dimension	MIN	NOM	MAX	MIN	NOM	MAX	
Number of Pins	n		8			8	
Pitch	р		.100			2.54	
Top to Seating Plane	Α	.160	.180	.200	4.06	4.57	5.08
Standoff §	A1	.020	.030	.040	0.51	0.77	1.02
Shoulder to Shoulder Width	Е	.290	.305	.320	7.37	7.75	8.13
Ceramic Pkg. Width	E1	.230	.265	.300	5.84	6.73	7.62
Overall Length	D	.370	.385	.400	9.40	9.78	10.16
Tip to Seating Plane	L	.125	.163	.200	3.18	4.13	5.08
Lead Thickness	С	.008	.012	.015	0.20	0.29	0.38
Upper Lead Width	B1	.045	.055	.065	1.14	1.40	1.65
Lower Lead Width	В	.016	.018	.020	0.41	0.46	0.51
Overall Row Spacing	eВ	.320	.360	.400	8.13	9.15	10.16

*Controlling Parameter JEDEC Equivalent: MS-030

Drawing No. C04-010

NOTES:



APPENDIX A: REVISION HISTORY

Revision A (February 2005)

• Original Release of this Document.



NOTES:



PRODUCT IDENTIFICATION SYSTEM

To order or obtain information, e.g., on pricing or delivery, refer to the factory or the listed sales office.

PART NO. Device and Temperature Package Range

TC4421M: 9A High-Speed MOSFET Driver, Inverting,

Temperature Range:

-55°C to +125°C TC4422M: 9A High-Speed MOSFET Driver, Non-Inverting,

-55°C to +125°C

Package: JA = Ceramic Dual In-Line (300 mil Body), 8-lead **Examples:**

TC4421MJA: 9A High-Speed MOSFET

Driver, Inverting, 8LD CERDIP package.

TC4422MJA: 9A High-Speed MOSFET

Driver, Non-Inverting, 8LD CERDIP package.



NOTES:



Note the following details of the code protection feature on Microchip devices:

- Microchip products meet the specification contained in their particular Microchip Data Sheet.
- Microchip believes that its family of products is one of the most secure families of its kind on the market today, when used in the intended manner and under normal conditions.
- There are dishonest and possibly illegal methods used to breach the code protection feature. All of these methods, to our
 knowledge, require using the Microchip products in a manner outside the operating specifications contained in Microchip's Data
 Sheets. Most likely, the person doing so is engaged in theft of intellectual property.
- · Microchip is willing to work with the customer who is concerned about the integrity of their code.
- Neither Microchip nor any other semiconductor manufacturer can guarantee the security of their code. Code protection does not
 mean that we are guaranteeing the product as "unbreakable."

Code protection is constantly evolving. We at Microchip are committed to continuously improving the code protection features of our products. Attempts to break Microchip's code protection feature may be a violation of the Digital Millennium Copyright Act. If such acts allow unauthorized access to your software or other copyrighted work, you may have a right to sue for relief under that Act.

Information contained in this publication regarding device applications and the like is provided only for your convenience and may be superseded by updates. It is your responsibility to ensure that your application meets with your specifications. MICROCHIP MAKES NO REPRESENTATIONS OR WAR-RANTIES OF ANY KIND WHETHER EXPRESS OR IMPLIED, WRITTEN OR ORAL, STATUTORY OR OTHERWISE, RELATED TO THE INFORMATION, INCLUDING BUT NOT LIMITED TO ITS CONDITION, QUALITY, PERFORMANCE, MERCHANTABILITY OR FITNESS FOR PURPOSE. Microchip disclaims all liability arising from this information and its use. Use of Microchip's products as critical components in life support systems is not authorized except with express written approval by Microchip. No licenses are conveyed, implicitly or otherwise, under any Microchip intellectual property rights.

Trademarks

The Microchip name and logo, the Microchip logo, Accuron, dsPIC, KEELOQ, microID, MPLAB, PIC, PICmicro, PICSTART, PRO MATE, PowerSmart, rfPIC, and SmartShunt are registered trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

AmpLab, FilterLab, Migratable Memory, MXDEV, MXLAB, PICMASTER, SEEVAL, SmartSensor and The Embedded Control Solutions Company are registered trademarks of Microchip Technology Incorporated in the U.S.A.

Analog-for-the-Digital Age, Application Maestro, dsPICDEM, dsPICDEM.net, dsPICworks, ECAN, ECONOMONITOR, FanSense, FlexROM, fuzzyLAB, In-Circuit Serial Programming, ICSP, ICEPIC, MPASM, MPLIB, MPLINK, MPSIM, PICkit, PICDEM, PICDEM.net, PICLAB, PICtail, PowerCal, PowerInfo, PowerMate, PowerTool, rfLAB, rfPICDEM, Select Mode, Smart Serial, SmartTel, Total Endurance and WiperLock are trademarks of Microchip Technology Incorporated in the U.S.A. and other countries.

SQTP is a service mark of Microchip Technology Incorporated in the U.S.A.

All other trademarks mentioned herein are property of their respective companies.

© 2005, Microchip Technology Incorporated, Printed in the U.S.A., All Rights Reserved.

Printed on recycled paper.

QUALITY MANAGEMENT SYSTEM CERTIFIED BY DNV ISO/TS 16949:2002 ==

Microchip received ISO/TS-16949:2002 quality system certification for its worldwide headquarters, design and wafer fabrication facilities in Chandler and Tempe, Arizona and Mountain View, California in October 2003. The Company's quality system processes and procedures are for its PICmicro® 8-bit MCUs, KEEL00® code hopping devices, Serial EEPROMs, microperipherals, nonvolatile memory and analog products. In addition, Microchip's quality system for the design and manufacture of development systems is ISO 9001:2000 certified.



WORLDWIDE SALES AND SERVICE

AMERICAS

Corporate Office

2355 West Chandler Blvd. Chandler, AZ 85224-6199 Tel: 480-792-7200 Fax: 480-792-7277 Technical Support:

http://support.microchip.com

Web Address: www.microchip.com

Atlanta

Alpharetta, GA Tel: 770-640-0034 Fax: 770-640-0307

Boston

Westford, MA Tel: 978-692-3848 Fax: 978-692-3821

Chicago Itasca, IL

Tel: 630-285-0071 Fax: 630-285-0075

Dallas

Addison, TX Tel: 972-818-7423 Fax: 972-818-2924

Detroit

Farmington Hills, MI Tel: 248-538-2250 Fax: 248-538-2260

Kokomo

Kokomo, IN Tel: 765-864-8360 Fax: 765-864-8387

Los Angeles

Mission Viejo, CA Tel: 949-462-9523 Fax: 949-462-9608

San Jose

Mountain View, CA Tel: 650-215-1444 Fax: 650-961-0286

Toronto

Mississauga, Ontario,

Canada

Tel: 905-673-0699 Fax: 905-673-6509

ASIA/PACIFIC

Australia - Sydney Tel: 61-2-9868-6733 Fax: 61-2-9868-6755

China - Beijing Tel: 86-10-8528-2100 Fax: 86-10-8528-2104

China - ChengduTel: 86-28-8676-6200
Fax: 86-28-8676-6599

China - Fuzhou

Tel: 86-591-8750-3506 Fax: 86-591-8750-3521

China - Hong Kong SAR Tel: 852-2401-1200

Fax: 852-2401-3431 China - Shanghai

Tel: 86-21-5407-5533 Fax: 86-21-5407-5066 China - Shenyang

Tel: 86-24-2334-2829 Fax: 86-24-2334-2393

China - Shenzhen

Tel: 86-755-8203-2660 Fax: 86-755-8203-1760

China - Shunde

Tel: 86-757-2839-5507 Fax: 86-757-2839-5571

China - Qingdao Tel: 86-532-502-7355 Fax: 86-532-502-7205

ASIA/PACIFIC

India - Bangalore Tel: 91-80-2229-0061 Fax: 91-80-2229-0062

India - New Delhi Tel: 91-11-5160-8631 Fax: 91-11-5160-8632

Japan - Kanagawa Tel: 81-45-471- 6166 Fax: 81-45-471-6122

Korea - Seoul Tel: 82-2-554-7200 Fax: 82-2-558-5932 o

82-2-558-5934

Singapore Tel: 65-6334-8870 Fax: 65-6334-8850

Taiwan - Kaohsiung Tel: 886-7-536-4818 **F**ax: 886-7-536-4803

Taiwan - Taipei Tel: 886-2-2500-6610 Fax: 886-2-2508-0102

Taiwan - Hsinchu Tel: 886-3-572-9526 Fax: 886-3-572-6459

EUROPE

Austria - Weis

Tel: 43-7242-2244-399 Fax: 43-7242-2244-393

Denmark - Ballerup Tel: 45-4450-2828 Fax: 45-4485-2829

France - Massy Tel: 33-1-69-53-63-20 Fax: 33-1-69-30-90-79

Germany - Ismaning Tel: 49-89-627-144-0 Fax: 49-89-627-144-44

Italy - Milan Tel: 39-0331-742611 Fax: 39-0331-466781

Netherlands - Drunen Tel: 31-416-690399 Fax: 31-416-690340

England - Berkshire Tel: 44-118-921-5869 Fax: 44-118-921-5820

10/20/04